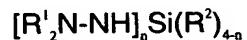


ABSTRACT OF THE DISCLOSURE

5 Processes for precursors for silicon dielectric depositions of silicon nitride, silicon oxide and silicon oxynitride on a substrate using a hydrazinosilane of the formula:



10 where each R¹ is independently selected from alkyl groups of C₁ to C₆; each R² is independently selected from the group consisting of hydrogen, alkyl, vinyl, allyl, and phenyl; and n = 1-4. Some of the hydrazinosilanes are novel precursors.